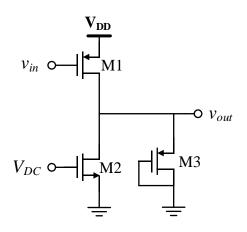
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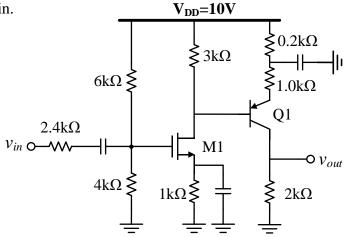
Technology

90 min

- 1- a) <u>Using the small-signal **model**</u>, determine a relation for the voltage gain  $(A_v = V_{out} / V_{in})$  of the following circuit. Assume that the transistors operate in saturation and  $\lambda \neq 0$ .
  - b) Determine  $R_{out}$ .

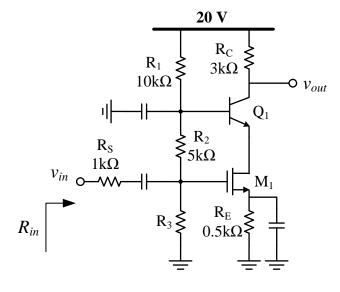


- 2- a) Determine the bias points of the transistors.
  - b) Calculate the voltage gain.



$$\begin{cases} V_{EB,on} = 0.6 \text{ V} \\ V_{EC,sat} = 0.2 \text{ V} \\ V_{TH} = 1 \text{ V} \\ \beta_{nmos} = 0.5 \text{ mA/V}^2 \\ \beta_{pnp} = 100 \\ V_A = 100V \\ \lambda = 0 \end{cases}$$

- 3- a) Specify  $R_3$  so that the bias current of the transistors will be equal to 2 mA. Prove that Q1 operates in forward active region.
  - b) Calculate the voltage gain ( $A_v = V_{out} / V_{in}$ ) and the input resistance ( $R_{in}$ ). Neglect the base current in DC analysis.



$$BJT: \begin{cases} V_{BE} = 0.7V \\ V_{CEsat} = 0.2V \end{cases}$$

$$V_{A} = \infty$$

$$V_{T} = 25mV$$

$$\beta = 100$$

$$V_{TH} = 2V$$

$$\mu_{n}C_{ox} = 0.5 \, mA \, / V^{2}$$

$$\lambda = \infty$$

$$\left(\frac{W}{L}\right) = \frac{2\mu m}{1\mu m}$$

## روابط قابل استفاده:

$$\begin{split} R_{seen-base} &= r_{\pi} + (\beta + 1)R_{E} \\ R_{seen-collector} &= r_{O}(1 + g_{m}(R_{E} \parallel r_{\pi})) \\ R_{seen-emitter} &= \frac{r_{O} + R_{C}}{1 + g_{m}r_{O}} \quad if \ (R_{B} = 0) \\ R_{seen-emitter} &= \frac{r_{\pi} + R_{B}}{\beta} \quad if \ (R_{B} \neq 0) \end{split}$$

$$A_{V,CE} = -g_m(R_C \parallel r_O)$$

$$A_{V,ED} = \frac{-R_C}{R_E + 1/g_m}$$

$$A_{V,CC} = \frac{R_E}{R_E + 1/g_m}$$

$$A_{V,CB} = g_m(R_C \parallel r_O)$$

